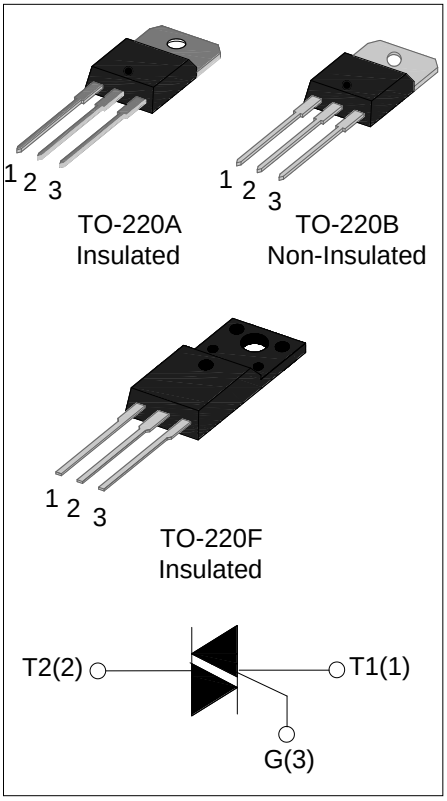
JST10 Series 10A TRIACs

Rev.2.0

DESCRIPTION:

JST10 series triacs, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products are recommended for use on inductive load. JST10A provides insulation voltage rated at 2500V RMS and JST10F provides insulation voltage rated at 2000V RMS from all three terminals to external heatsink complying with UL standards (File ref: E252906).



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	10	A
V_{DRM} /V_{RRM}	600 and 800	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	℃
Operating junction temperature range		T_j	-40 - 125	℃
Repetitive peak off-state voltage (T_j=25℃)		V_{DRM}	600/800	V
Repetitive peak reverse voltage (T_j=25℃)		V_{RRM}	600/800	V
Non repetitive surge peak Off-state voltage		V_{DSM}	V_{DRM} +100	V
Non repetitive peak reverse voltage		V_{RSM}	V_{RRM} +100	V
RMS on-state current	TO-220A(Ins) (T_C=88℃)	$I_{T(RMS)}$	10	A
	TO-220B(Non-Ins) (T_C=110℃)			
	TO-220F(Ins) (T_C=97℃)			
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	100	A

I^2t value for fusing (tp=10ms)	I^2t	50	A^2s
Critical rate of rise of on-state current (I_G =2×I_{GT})	dI/dt	50	A/μs
Peak gate current	I_{GM}	2	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value		Unit
				CW	BW	
I_{GT}	V_D =12V R_L =33Ω	Ⅰ-Ⅱ-Ⅲ	MAX	35	50	mA
V_{GT}		Ⅰ-Ⅱ-Ⅲ	MAX	1.5		V
V_{GD}	V_D =V_{DRM} T_j =125℃ R_L =3.3KΩ	Ⅰ-Ⅱ-Ⅲ	MIN	0.2		V
I_L	I_G =1.2I_{GT}	Ⅰ-Ⅲ	MAX	50	70	mA
		Ⅱ		60	80	
I_H	I_T =100mA		MAX	40	60	mA
dV/dt	V_D=2/3V_{DRM} Gate Open T_j =125℃		MIN	400	1000	V/μs
(dV/dt)c	(dI/dt)c=1.8A/ms T_j =125℃		MIN	6.5	12	V/μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I_{TM}=16A tp=380μs	T_j=25℃	1.55	V
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25℃	5	μA
I_{RRM}		T_j=125℃	1	mA

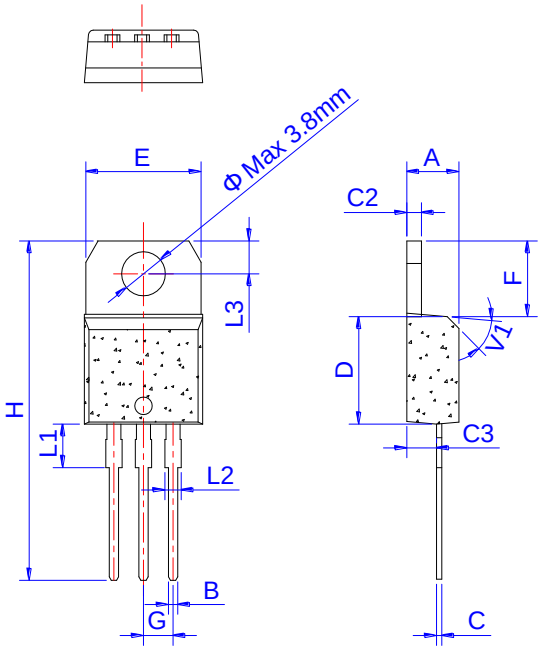
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)	4.2	℃/W
		TO-220B(Non-Ins)	2.4	
		TO-220F(Ins)	3.3	

ORDERING INFORMATION

J	ST	10	A	-600	CW
JieJie Microelectronics Co.,Ltd	Triacs	$I_{T(RMS)}$:10A	A:TO-220A(Ins) F:TO-220F(Ins) B:TO-220B(Non-Ins)	600:V_{DRM} /V_{RRM}≥600V 800:V_{DRM} /V_{RRM}≥800V	CW: I_{GT1-3}≤35mA BW: I_{GT1-3}≤50mA

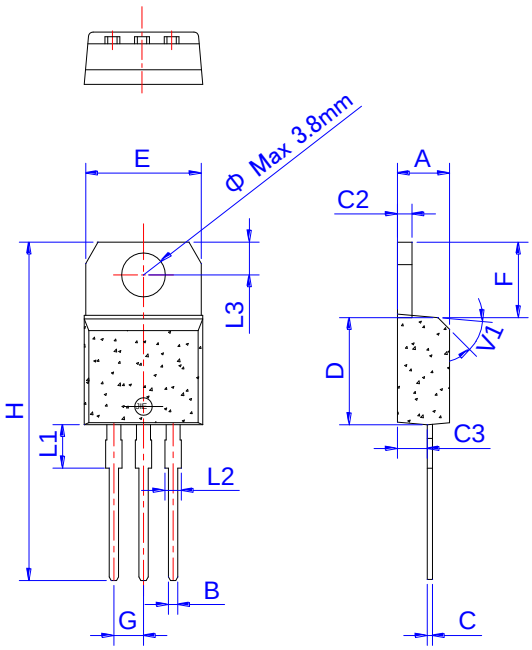
PACKAGE MECHANICAL DATA



TO-220A Ins

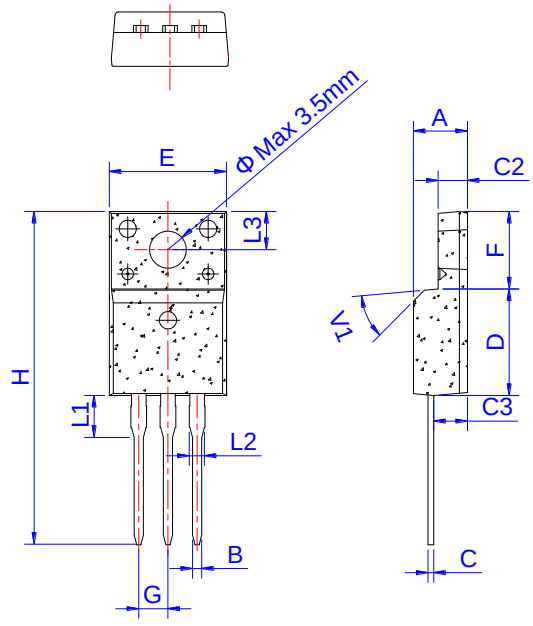
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA



TO-220B Non-Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



TO-220F Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.48		0.75	0.019		0.030
C2	2.40		2.70	0.094		0.106
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.70		10.3	0.382		0.406
F	6.40		7.00	0.252		0.276
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

FIG.1: Maximum power dissipation versus RMS on-state current

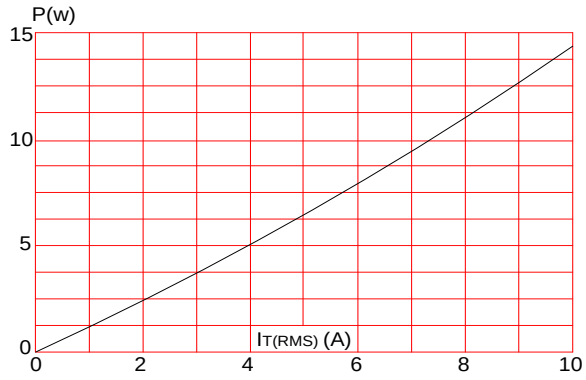


FIG.2: RMS on-state current versus case temperature

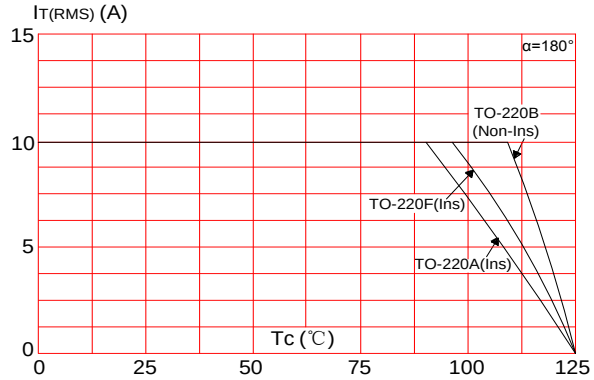


FIG.3: Surge peak on-state current versus number of cycles

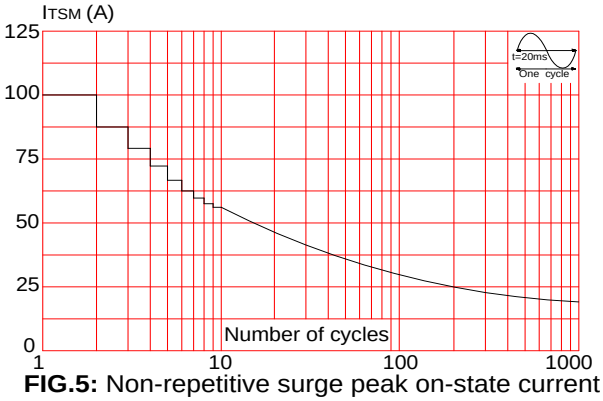


FIG.4: On-state characteristics (maximum values)

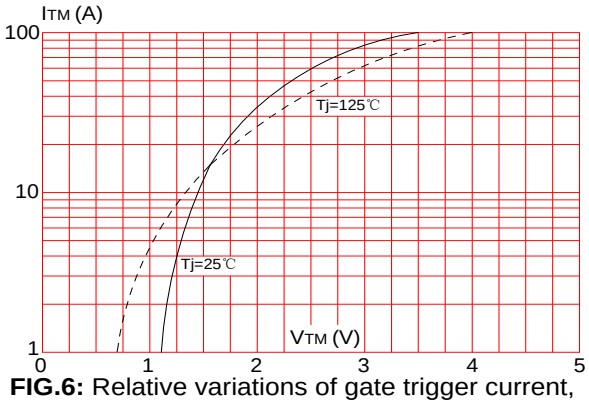


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t (dI/dt < 50A/μs)

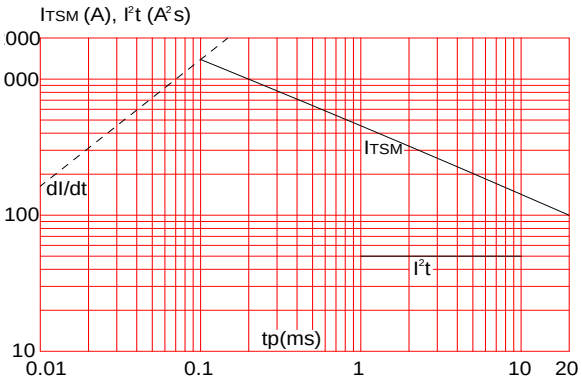
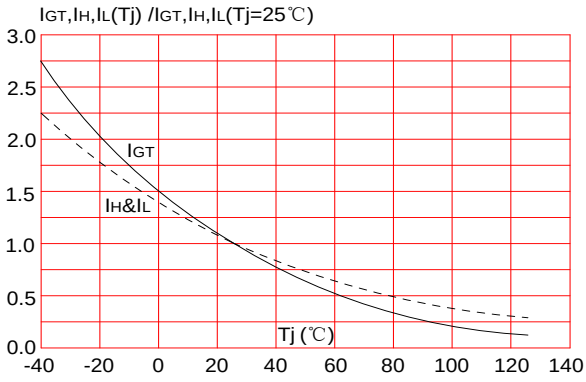


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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